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Semiconductor device and producing method thereof

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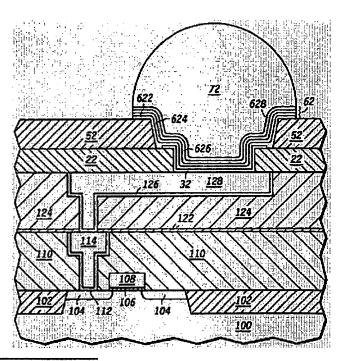
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Abstract not available for CN1269607 Abstract of correspondent: **US2002000665**

An interconnect overlies a semiconductor device substrate (10). In one embodiment, a conductive barrier layer overlies a portion of the interconnect, a passivation layer (92) overlies the conductive barrier layer and the passivation layer (92) has an opening that exposes portions of the conductive barrier layer (82). In an alternate embodiment a passivation layer (22) overlies the interconnect, the passivation layer (22) has an opening (24) that exposes the interconnect and a conductive barrier layer (32) overlies the interconnect within the opening (24).



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